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4. (Previously Amended) A semiconductor device according to claim 2, wherein the openings comprise a pattern of radiating channels disposed about a center of the bonding surface.

- 5. A semiconductor device according to claim 2, wherein the openings comprise a series of spaced apart rectangular channels arranged parallel to one another.
- 6. A semiconductor device according to claim 2, wherein the openings comprise an array of L shaped channels disposed about a center of the bonding surface.
- 7. A semiconductor device according to claim 2, wherein the openings comprise an array of holes disposed about the bonding surface.
  - 8. (Previously Amended) A semiconductor device, which comprises:
  - a. an active circuit in the semiconductor device;
  - b. a wiring pattern overlying and in electrical contact with the active circuit;
  - c. bond pads formed as select areas on the wiring pattern; and
  - d. a plurality of openings extending into a substantially flat bonding surface of the bond pads.
- 9. A semiconductor device according to claim 8, wherein the openings are disposed about a center portion of the bonding surface of the bond pad so that the center portion of the bonding surface is free of openings.
- 10. A semiconductor device according to claim 8, wherein the openings comprise a pattern of radiating channels disposed about a center of the bonding surface.
- 11. A semiconductor device according to claim 8, wherein the openings comprise a series of spaced apart rectangular channels arranged parallel to one another.

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19. An improved bond pad according to claim 18, wherein the openings are disposed about a center portion of the planar surface of the bond pad so that the center portion of the planar surface is free of openings.

- 20. An improved bond pad according to claim 18, wherein the openings comprise a pattern of radiating channels disposed about a center of the bond pad.
- 21. An improved bond pad according to claim 18, wherein the openings comprise a series of spaced apart rectangular channels arranged parallel to one another.
- 22. An improved bond pad according to claim 18, wherein the openings comprise an array of L shaped channels disposed about a center of the bond pad.
- 23. An improved bond pad according to claim 18, wherein the openings comprise an array of holes disposed about the bond pad.
- 24. An improved bond pad according to claim 18, further comprising a passivation layer overlying the metal layer, the passivation layer having holes therethrough to expose the planar surface of the bond pad to enable electrical connection to the bond pad.
- 25. An improved bond pad according to claim 18, further comprising a bond wire bonded to the planar surface of the bond pad.
- 26. An improved bond pad according to claim 18, wherein said metal layer is aluminum.

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27. (Twice Amended) A semiconductor device having an improved bond pad, the semiconductor device comprising:

a bond pad electrically connected to an active circuit of the semiconductor device, said bond pad having a substantially planar surface; and

at least one opening extending into said bond pad.

28. (Twice Amended) A semiconductor device having an improved bond pad, the bond pad having a metal layer, said metal layer having a substantially planar surface connected to an active circuit of a semiconductor device further having at least one opening extending therethrough, the semiconductor device made according to the method comprising:

forming a thick insulating layer over active circuitry of a semiconductor chip;

etching said thick insulating layer thereby forming clear contact paths to said active circuitry of the semiconductor chip;

forming a metal layer over said thick insulating layer; and

etching said metal layer thereby forming an interconnect wiring pattern and bond pads
having at least one opening extending into said bond pads

29. (Amended) A semiconductor device according to claim 28 further comprising: forming a passivation layer over the metal layer; and etching said passivation layer to expose select areas of the wiring pattern and bond pads.